

High Voltage Power MOSFET

IXTH05N250P3HV

$$V_{DSS} = 2500V$$

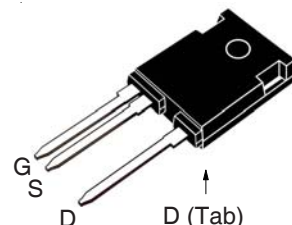
$$I_{D25} = 0.50A$$

$$R_{DS(on)} \leq 110\Omega$$

N-Channel Enhancement Mode



TO-247HV



G = Gate D = Drain
S = Source Tab = Drain

| Symbol | Test Conditions | Maximum Ratings | |
|---------------|---|-----------------|------------------|
| V_{DSS} | $T_J = 25^\circ\text{C}$ to 150°C | 2500 | V |
| V_{DGR} | $T_J = 25^\circ\text{C}$ to 150°C , $R_{GS} = 1M\Omega$ | 2500 | V |
| V_{GSS} | Continuous | ± 20 | V |
| V_{GSM} | Transient | ± 30 | V |
| I_{D25} | $T_C = 25^\circ\text{C}$ | 0.50 | A |
| I_{D110} | $T_C = 110^\circ\text{C}$ | 0.33 | A |
| I_{DM} | $T_C = 25^\circ\text{C}$, Pulse Width Limited by T_{JM} | 1.00 | A |
| P_D | $T_C = 25^\circ\text{C}$ | 104 | W |
| T_J | | - 55 ... +150 | $^\circ\text{C}$ |
| T_{JM} | | 150 | $^\circ\text{C}$ |
| T_{stg} | | - 55 ... +150 | $^\circ\text{C}$ |
| T_L | Maximum Lead Temperature for Soldering | 300 | $^\circ\text{C}$ |
| T_{SOLD} | 1.6 mm (0.062in.) from Case for 10s | 260 | $^\circ\text{C}$ |
| M_d | Mounting Torque | 1.13/10 | Nm/lb.in |
| Weight | | 6 | g |

Features

- High Blocking Voltage
- High Voltage Package

Advantages

- Easy to Mount
- Space Savings
- High Power Density

Applications

- High Voltage Power Supplies
- Capacitor Discharge Applications
- Pulse Circuits
- Laser and X-Ray Generation Systems

| Symbol | Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified) | Characteristic Values | | |
|--------------|---|-----------------------|------|---------------------------------------|
| | | Min. | Typ. | Max. |
| BV_{DSS} | $V_{GS} = 0V$, $I_D = 250\mu\text{A}$ | 2500 | | V |
| $V_{GS(th)}$ | $V_{DS} = V_{GS}$, $I_D = 250\mu\text{A}$ | 2.0 | | 4.0 V |
| I_{GSS} | $V_{GS} = \pm 20V$, $V_{DS} = 0V$ | | | ± 100 nA |
| I_{DSS} | $V_{DS} = 0.8 \cdot V_{DSS}$, $V_{GS} = 0V$ $T_J = 125^\circ\text{C}$ | | | 10 μA 250 μA |
| $R_{DS(on)}$ | $V_{GS} = 10V$, $I_D = 0.25A$, Note 1 | | | 110 Ω |

| Symbol | Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified) | Characteristic Values | | |
|--------------|---|-----------------------|------|------------------------|
| | | Min. | Typ. | Max. |
| g_{fs} | $V_{DS} = 60\text{V}$, $I_D = 0.25\text{A}$, Note 1 | 0.19 | 0.32 | S |
| C_{iss} | $V_{GS} = 0\text{V}$, $V_{DS} = 25\text{V}$, $f = 1\text{MHz}$ | | 303 | pF |
| C_{oss} | | | 24 | pF |
| C_{rss} | | | 6 | pF |
| $t_{d(on)}$ | Resistive Switching Times $V_{GS} = 10\text{V}$, $V_{DS} = 50\text{V}$, $I_D = 0.50\text{A}$ $R_G = 10\Omega$ (External) | | 11 | ns |
| t_r | | | 20 | ns |
| $t_{d(off)}$ | | | 23 | ns |
| t_f | | | 21 | ns |
| $Q_{g(on)}$ | $V_{GS} = 10\text{V}$, $V_{DS} = 1.1\text{kV}$, $I_D = 0.5 \cdot I_{D25}$ | | 10.5 | nC |
| Q_{gs} | | | 1.3 | nC |
| Q_{gd} | | | 7.2 | nC |
| R_{thJC} | | | | 1.2 $^\circ\text{C/W}$ |
| R_{thCS} | | 0.21 | | $^\circ\text{C/W}$ |

TO-247HV (IXTH) Outline

PINS:
1 - Gate 2 - Source
3, 4 - Drain

| SYM | INCHES | | MILLIMETERS | |
|-----------|--------|------|-------------|-------|
| | MIN | MAX | MIN | MAX |
| A | .193 | .201 | 4.90 | 5.10 |
| A1 | .114 | .122 | 2.90 | 3.10 |
| A2 | .075 | .083 | 1.90 | 2.10 |
| A3 | .035 | .043 | 0.90 | 1.10 |
| b | .053 | .059 | 1.35 | 1.50 |
| b1 | .075 | .083 | 1.90 | 2.10 |
| c | .022 | .030 | 0.55 | 0.75 |
| D | .819 | .843 | 20.80 | 21.40 |
| D1 | .638 | .646 | 16.20 | 16.40 |
| D2 | .134 | .146 | 3.40 | 3.70 |
| D3 | .055 | .063 | 1.40 | 1.60 |
| E | .622 | .638 | 15.80 | 16.20 |
| E1 | .520 | .528 | 13.20 | 13.40 |
| E2 | .118 | .126 | 3.00 | 3.20 |
| E3 | .051 | .059 | 1.30 | 1.50 |
| e | .100 | BSC | 2.54 | BSC |
| e1 | .300 | BSC | 7.62 | BSC |
| L | .732 | .748 | 18.60 | 19.00 |
| L1 | .106 | .118 | 2.70 | 3.00 |
| ϕP | .138 | .142 | 3.50 | 3.60 |
| $\phi P1$ | .272 | .280 | 6.90 | 7.10 |
| Q | .216 | .224 | 5.50 | 5.70 |
| R | .165 | .169 | 4.20 | 4.30 |
| S | .240 | .248 | 6.10 | 6.30 |

Source-Drain Diode

| Symbol | Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified) | Characteristic Values | | |
|----------|---|-----------------------|------|---------------|
| | | Min. | Typ. | Max |
| I_S | $V_{GS} = 0\text{V}$, Note 1 | | | 0.5 A |
| I_{SM} | Repetitive, pulse Width Limited by T_{JM} | | | 2.0 A |
| V_{SD} | $I_F = I_S$, $V_{GS} = 0\text{V}$, Note 1 | | | 1.5 V |
| t_{rr} | $I_F = 0.5\text{A}$, $-di/dt = 100\text{A}/\mu\text{s}$ $V_R = 100\text{V}$ | | 1.2 | μs |
| Q_{RM} | | | 7.0 | μC |
| I_{RM} | | | 12.2 | A |

Note: 1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.

ADVANCE TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

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| | | | | | | | | | | |
|--|-----------|-----------|-----------|-----------|--------------|--------------|--------------|--------------|--------------|-------------|
| IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: | 4,835,592 | 4,931,844 | 5,049,961 | 5,237,481 | 6,162,665 | 6,404,065 B1 | 6,683,344 | 6,727,585 | 7,005,734 B2 | 7,157,338B2 |
| | 4,860,072 | 5,017,508 | 5,063,307 | 5,381,025 | 6,259,123 B1 | 6,534,343 | 6,710,405 B2 | 6,759,692 | 7,063,975 B2 | |
| | 4,881,106 | 5,034,796 | 5,187,117 | 5,486,715 | 6,306,728 B1 | 6,583,505 | 6,710,463 | 6,771,478 B2 | 7,071,537 | |

Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

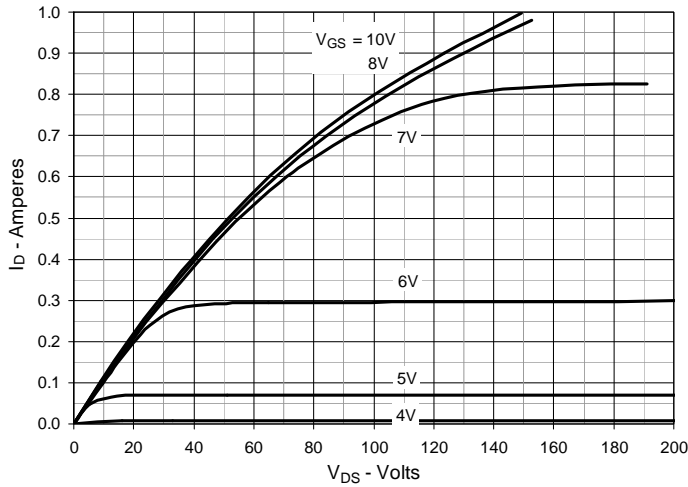


Fig. 2. Output Characteristics @ $T_J = 125^\circ\text{C}$

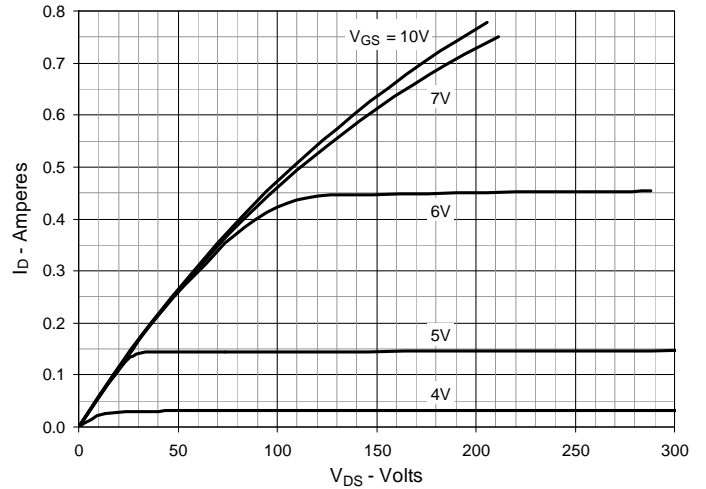


Fig. 3. $R_{DS(on)}$ Normalized to $I_D = 0.25\text{A}$ Value vs. Junction Temperature

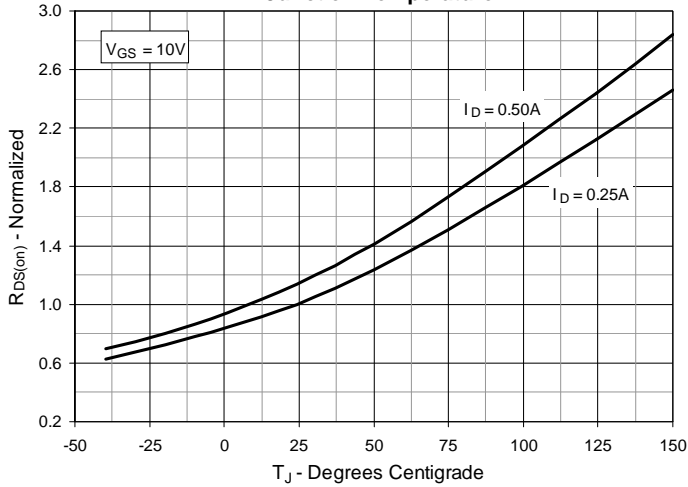


Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 0.25\text{A}$ Value vs. Drain Current

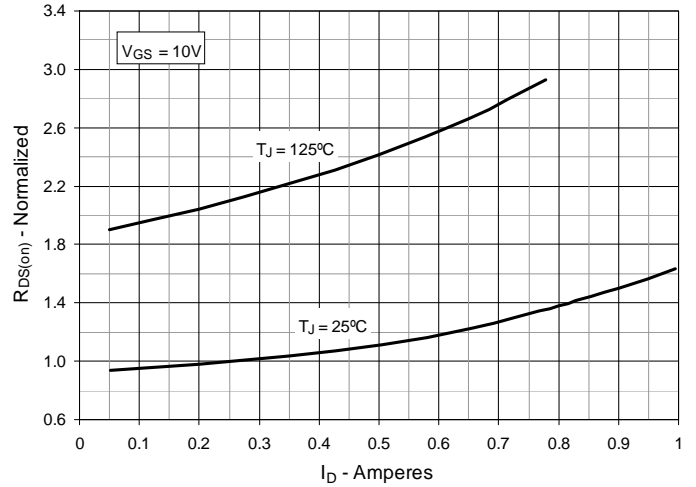


Fig. 5. Maximum Drain Current vs. Case Temperature

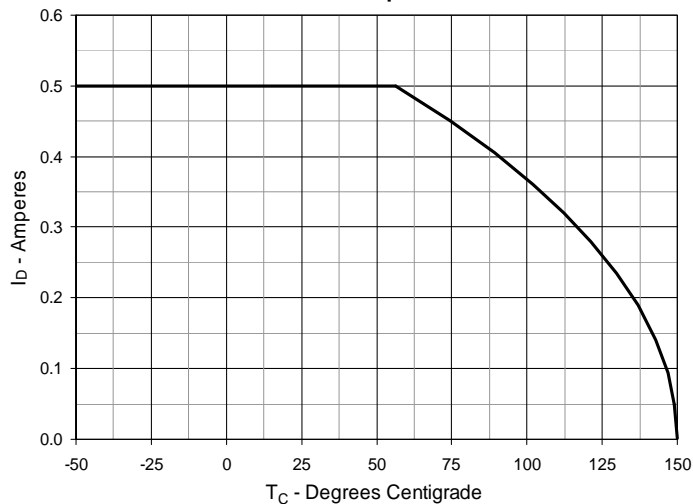


Fig. 6. Input Admittance

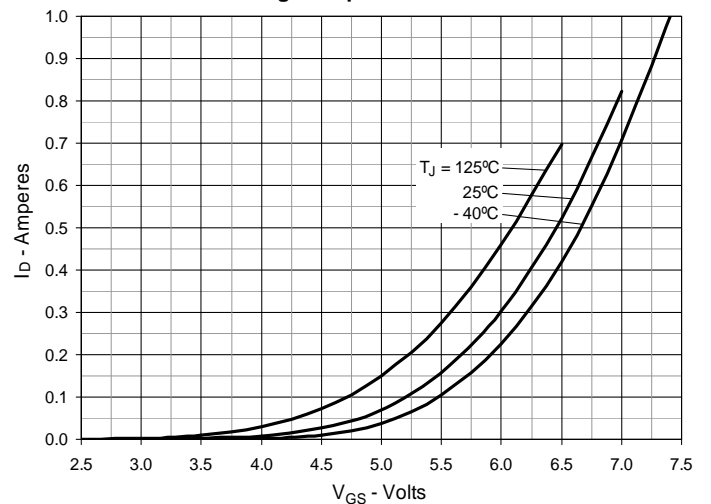


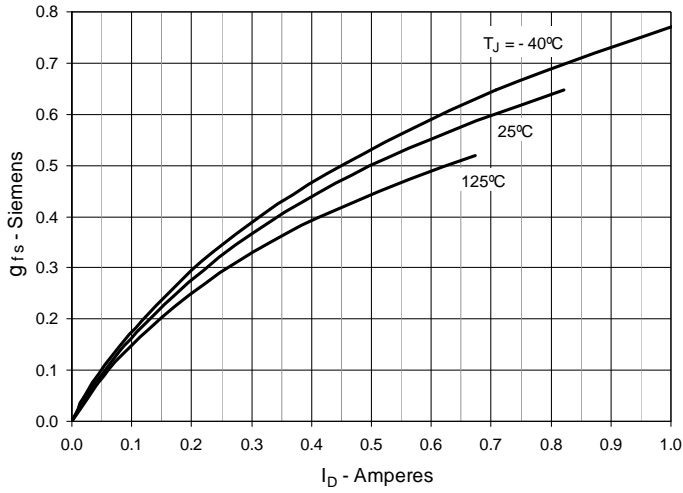
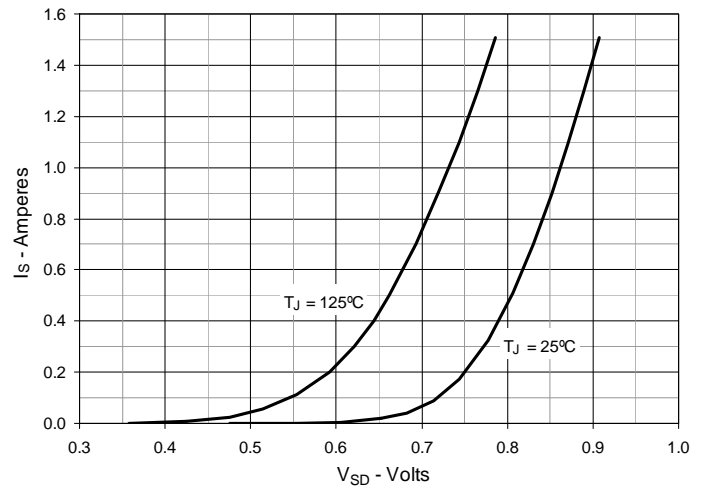
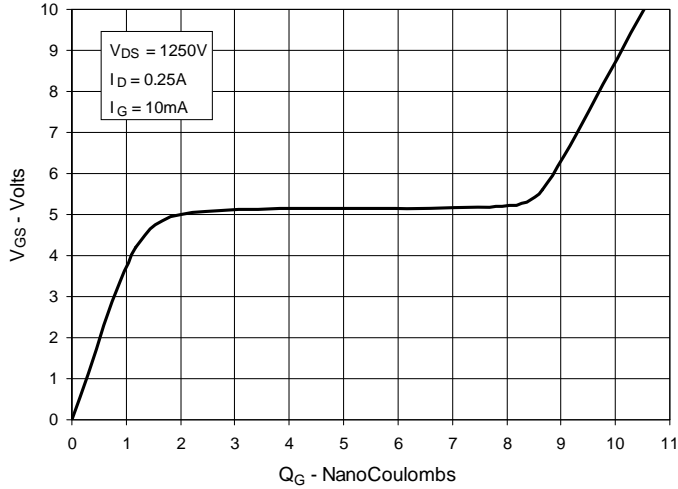
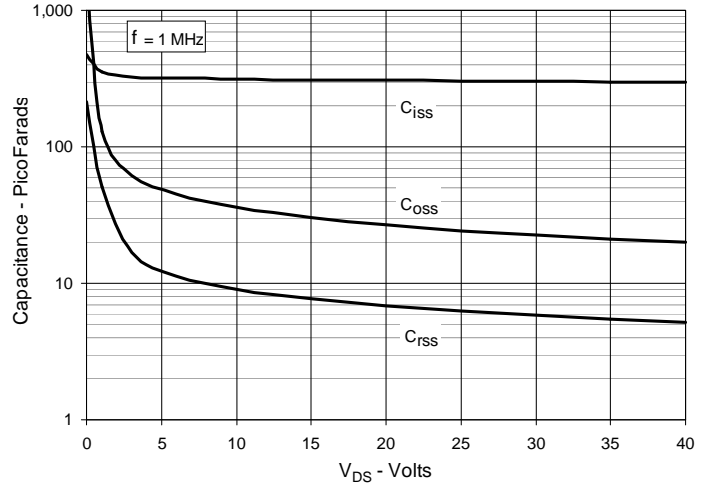
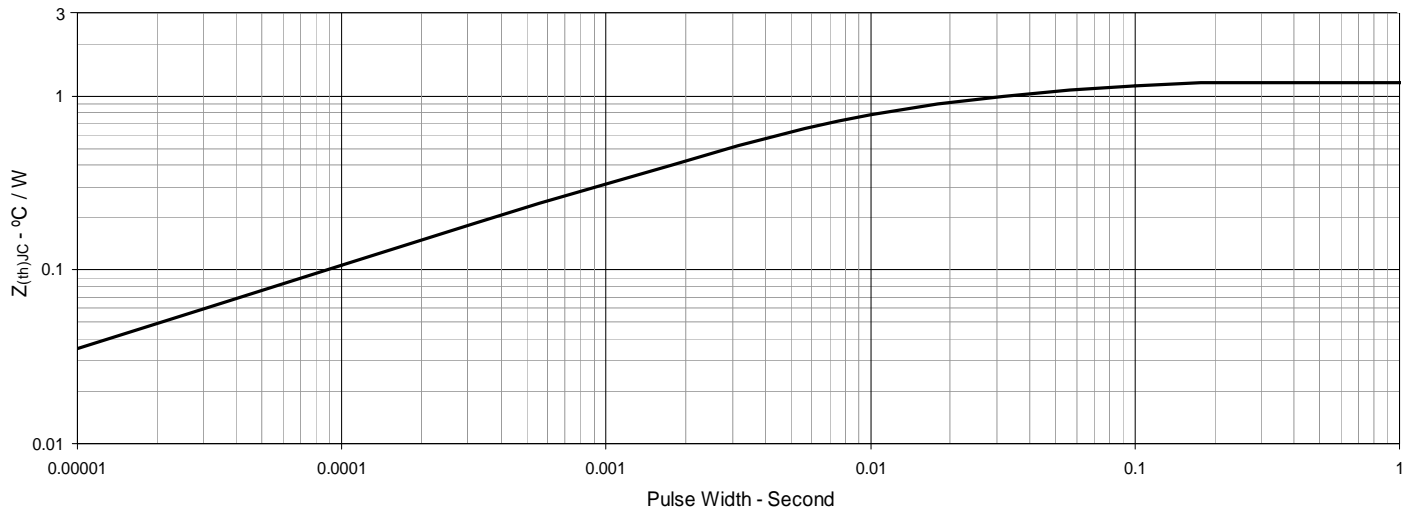
Fig. 7. Transconductance

Fig. 8. Forward Voltage Drop of Intrinsic Diode

Fig. 9. Gate Charge

Fig. 10. Capacitance

Fig. 11. Maximum Transient Thermal Impedance


Fig. 12. Forward-Bias Safe Operating Area
@ $T_C = 25^\circ\text{C}$

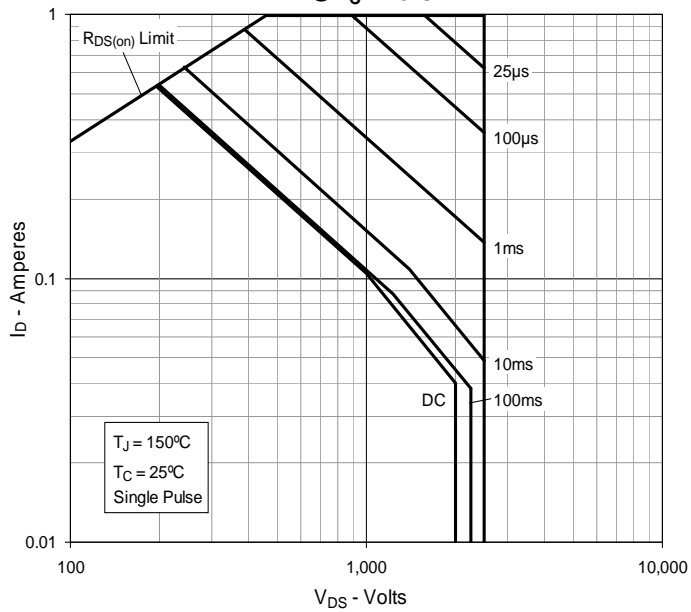
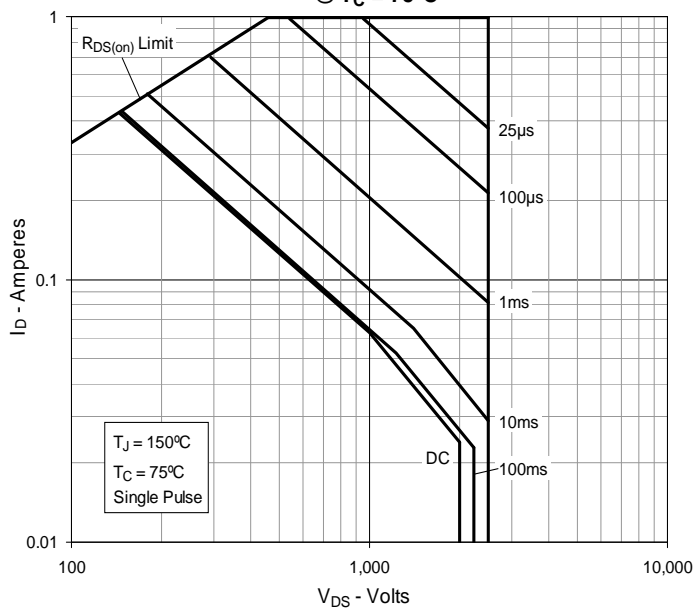


Fig. 13. Forward-Bias Safe Operating Area
@ $T_C = 75^\circ\text{C}$





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